

Kelson D Chabak

List of Publications by Year in descending order

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28
papers

2,823
citations

304743

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580821

25
g-index

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docs citations

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times ranked

1646
citing authors

#	ARTICLE	IF	CITATIONS
1	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped $\text{Ga}_{2-x}\text{O}_{3-x}\text{MOSFETs}$. IEEE Electron Device Letters, 2016, 37, 902-905.	3.9	468
2	Enhancement-mode Ga_2O_3 wrap-gate fin field-effect transistors on native (100) Ga_2O_3 substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	3.3	298
3	Demonstration of high mobility and quantum transport in modulation-doped $\text{In}^{2-}(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterostructures. Applied Physics Letters, 2018, 112, .	3.3	264
4	In^{2-} Ga_2O_3 MOSFETs for Radio Frequency Operation. IEEE Electron Device Letters, 2017, 38, 790-793.	3.9	248
5	Donors and deep acceptors in In^{2-} Ga_2O_3 . Applied Physics Letters, 2018, 113, .	3.3	203
6	Recessed-Gate Enhancement-Mode In^{2-} Ga_2O_3 MOSFETs. IEEE Electron Device Letters, 2018, 39, 67-70.	3.9	187
7	In^{2-} Gallium oxide power electronics. APL Materials, 2022, 10, .	5.1	184
8	Ge-Doped In^{2-} Ga_2O_3 MOSFETs. IEEE Electron Device Letters, 2017, 38, 775-778.	3.9	165
9	Highly conductive homoepitaxial Si-doped Ga_2O_3 films on (010) In^{2-} Ga_2O_3 by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	128
10	Lateral In^{2-} $\text{Ga}_{2-x}\text{O}_{3-x}$ field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	2.0	85
11	Incomplete Ionization of a 110 meV Unintentional Donor in In^{2-} Ga_2O_3 and its Effect on Power Devices. Scientific Reports, 2017, 7, 13218.	3.3	84
12	High pulsed current density In^{2-} Ga_2O_3 MOSFETs verified by an analytical model corrected for interface charge. Applied Physics Letters, 2017, 110, .	3.3	75
13	ScAlN/GaN High-Electron-Mobility Transistors With 2.4-A/mm Current Density and 0.67-S/mm Transconductance. IEEE Electron Device Letters, 2019, 40, 1056-1059.	3.9	63
14	High Aspect Ratio In^{2-} $\text{Ga}_{2-x}\text{O}_{3-x}$ Fin Arrays with Low-Interface Charge Density by Inverse Metal-Assisted Chemical Etching. ACS Nano, 2019, 13, 8784-8792.	14.6	57
15	Implementation of High-Power-Density In^{2-} $\text{Ga}_{2-x}\text{O}_{3-x}$ Band AlGaN/GaN High Electron Mobility Transistors in a Millimeter-Wave Monolithic Microwave Integrated Circuit Process. IEEE Electron Device Letters, 2015, 36, 1004-1007.	3.9	50
16	RF Power Performance of Sc(Al,Ga)N/GaN HEMTs at Ka-Band. IEEE Electron Device Letters, 2020, 41, 1181-1184.	3.9	41
17	Si content variation and influence of deposition atmosphere in homoepitaxial Si-doped In^{2-} $\text{Ga}_{2-x}\text{O}_{3-x}$ films by pulsed laser deposition. APL Materials, 2018, 6, 101102.	5.1	40
18	Thin channel In^{2-} $\text{Ga}_{2-x}\text{O}_{3-x}$ MOSFETs with self-aligned refractory metal gates. Applied Physics Express, 2019, 12, 126501.	2.4	35

#	ARTICLE	IF	CITATIONS
19	Pulsed Power Performance of $\text{In}^2\text{-GaAs}$ MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992.	3.9	32
20	Strained AlInN/GaN HEMTs on SiC With 2.1-A/mm Output Current and 104-GHz Cutoff Frequency. IEEE Electron Device Letters, 2010, 31, 561-563.	3.9	25
21	Toward high voltage radio frequency devices in $\text{In}^2\text{-Ga}_2\text{O}_3$. Applied Physics Letters, 2020, 117, .	3.3	23
22	Electrical and chemical analysis of Ti/Au contacts to $\text{In}^2\text{-Ga}_2\text{O}_3$. APL Materials, 2021, 9, 061104.	5.1	23
23	Self-Heating Characterization of $\text{In}^2\text{-Ga}_2\text{O}_3$ Thin-Channel MOSFETs by Pulsed I^2V and Raman Nanothermography. IEEE Transactions on Electron Devices, 2020, 67, 204-211.	3.0	18
24	Thermally-Aware Layout Design of $\text{In}^2\text{-GaAs}$ Lateral MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1251-1257.	3.0	11
25	Scaled T-Gate $\text{In}^2\text{-Ga}_2\text{O}_3$ MESFETs With 2.45 kV Breakdown and High Switching Figure of Merit. IEEE Electron Device Letters, 2022, 43, 1307-1310.	3.9	8
26	Gate-recessed, laterally-scaled $\text{In}^2\text{-GaAs}$ MOSFETs with high-voltage enhancement-mode operation. , 2017, , .		7
27	Towards the Integration of $\text{Hf}_{0.8}\text{Zr}_{0.2}\text{O}_2$ -based Negative Capacitance Dielectrics on $\text{In}^2\text{-Ga}_2\text{O}_3$ Substrates. , 2021, , .		1
28	Field-Effect Transistors 1. Springer Series in Materials Science, 2020, , 563-582.	0.6	0